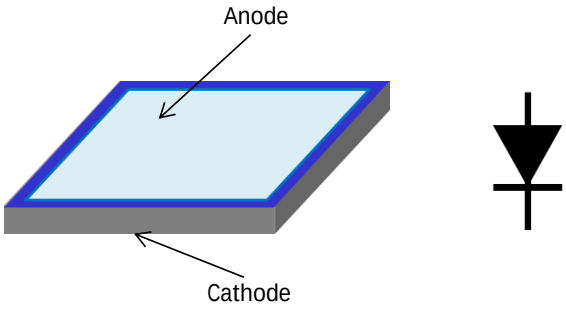
YJ Planar Schottky Barrier Diode Die Specification

80V 0.5A, 23mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB023L080AS-180A



Main Products Characterstics

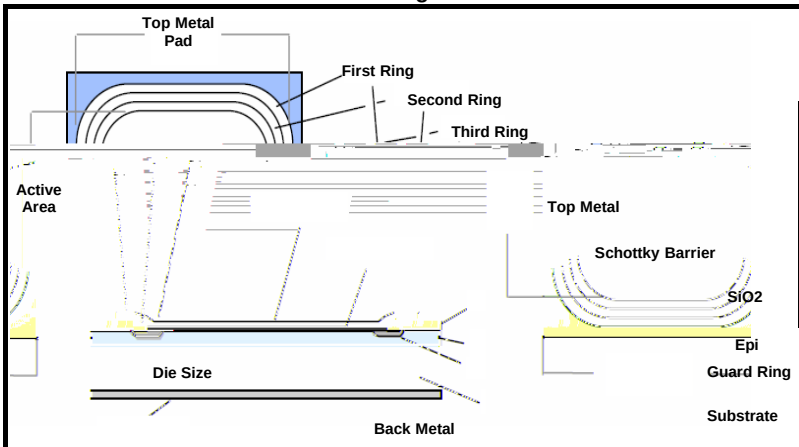
Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	80 V
Average forward current	$I_{F(AV)}$	0.5 A
(tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	10 A
Storage temperature range	T_{stg}	-50 to +125 °C
Maximum operating junction temperature	T_j	125 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage I_R = 1mA	V_{BR}	80 V	88.5V
Maximum forward voltage drop I_F = 0.5A 2%	V_F	0.8V	0.73V
Maximum reverse current V_R = 25V 2%	I_R	50uA	0.96uA

Device Schematics and Outline Drawing



Die Thickness *	180um
Die Size **	23 Mils
Top Metal Pad	20.2 Mils
Active Area	17.6 Mils
Top Metal	AL/3.5um
Back Metal	Ag/1.5um
Steet width	70um

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.